TO SEPARATE, HOLD TOP AND BOTTOM EDGES, SNAP-APART AND DISCARD CARBON

FORM PTO-892 (REV. 2-92) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	SERIAL NO.	GROUP ART UNIT	ATTACHMENT TO PAPER NUMBER
NOTICE OF REFERENCES CITED	09-682,863	2817	13
	APPLICANT(S) McGrath		

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*		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
	A	6344663	2-5-2002	Slater, Jr et al.	257	77	
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						
	J						
	K						

FOREIGN PATENT DOCUMENTS

*		DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG	PERTINENT PP. SPEC.
	L	58130608	8-4-1983	Japan	Onishi et al.	—	—		
	M								
	N								
	O								
	P								
	Q								

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EXAMINER	DATE
MICHAEL B SHINGLETON	4-3-03

* A copy of this reference is not being furnished with this office action.
(See Manual of Patent Examining Procedure, section 707.05 (a).)